

N-Channel Enhancement Mode Power MOSFET

Description

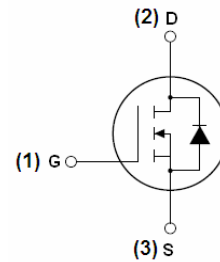
The PTP7190 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

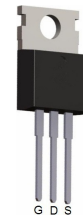
- $V_{DS} = 71V, I_D = 90A$
 $R_{DS(ON)} < 6.8m\Omega @ V_{GS}=10V$ (Typ:5.9m Ω)
- Special process technology for high ESD capability
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply



Schematic diagram



TO-220-3L top view

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|--------------------|----------|------|
| Drain-Source Voltage | V_{DS} | 71 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | 90 | A |
| Drain Current-Continuous($T_C=100^\circ C$) | $I_D(100^\circ C)$ | 63 | A |
| Pulsed Drain Current | I_{DM} | 320 | A |
| Maximum Power Dissipation | P_D | 170 | W |

| | | | |
|--|----------------|------------|------|
| Derating factor | | 1.13 | W/°C |
| Single pulse avalanche energy (Note 5) | E_{AS} | 550 | mJ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 175 | °C |

Thermal Characteristic

| | | | |
|---|-----------------|------|------|
| Thermal Resistance, Junction-to-Case (Note 2) | $R_{\theta JC}$ | 0.88 | °C/W |
|---|-----------------|------|------|

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

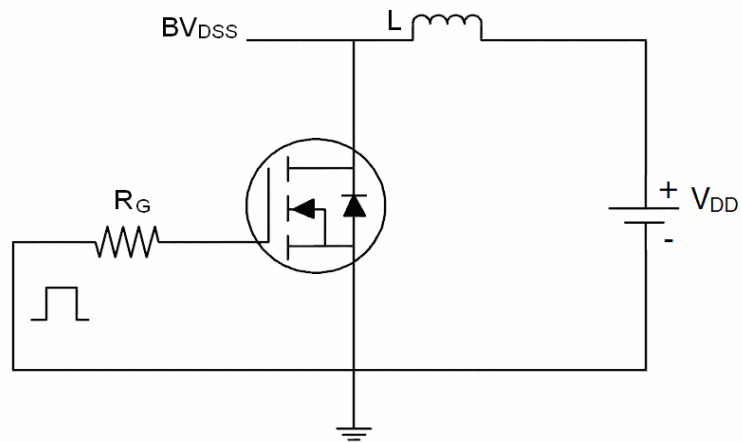
| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|--------------|--|-----|-------|-----------|------------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 71 | 74 | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=71V, V_{GS}=0V$ | - | - | 1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | - | - | ± 100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 2 | 3 | 4 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}=10V, I_D=40A$ | - | 5.9 | 6.8 | m Ω |
| Forward Transconductance | g_{FS} | $V_{DS}=10V, I_D=40A$ | - | 50 | - | S |
| Dynamic Characteristics (Note 4) | | | | | | |
| Gate resistance | R_g | $V_{DS}=0V, V_{GS}=0V, F=1.0\text{MHz}$ | - | 0.63 | - | Ω |
| Input Capacitance | C_{iss} | $V_{DS}=15V, V_{GS}=0V,$ $F=1.0\text{MHz}$ | - | 4871 | - | PF |
| Output Capacitance | C_{oss} | | - | 630.6 | - | PF |
| Reverse Transfer Capacitance | C_{rss} | | - | 410.3 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=30V, I_D=42A$ $V_{GS}=10V, R_{GEN}=10\Omega$ | - | 36.1 | - | nS |
| Turn-on Rise Time | t_r | | - | 54.3 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 85.2 | - | nS |
| Turn-Off Fall Time | t_f | | - | 37.3 | - | nS |
| Total Gate Charge | Q_g | $V_{DS}=48V, I_D=84A,$ $V_{GS}=10V$ | - | 85.7 | - | nC |
| Gate-Source Charge | Q_{gs} | | - | 23.2 | - | nC |
| Gate-Drain Charge | Q_{gd} | | - | 31.2 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 3) | V_{SD} | $V_{GS}=0V, I_S=20A$ | - | - | 1.2 | V |
| Diode Forward Current (Note 2) | I_S | - | - | - | 90 | A |
| Reverse Recovery Time | t_{rr} | $T_J = 25^\circ\text{C}, I_F = 84A$ $di/dt = 100A/\mu\text{s}(\text{Note 3})$ | - | 88.3 | - | nS |
| Reverse Recovery Charge | Q_{rr} | | - | 65.9 | - | nC |
| Forward Turn-On Time | t_{on} | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | | |

Notes:

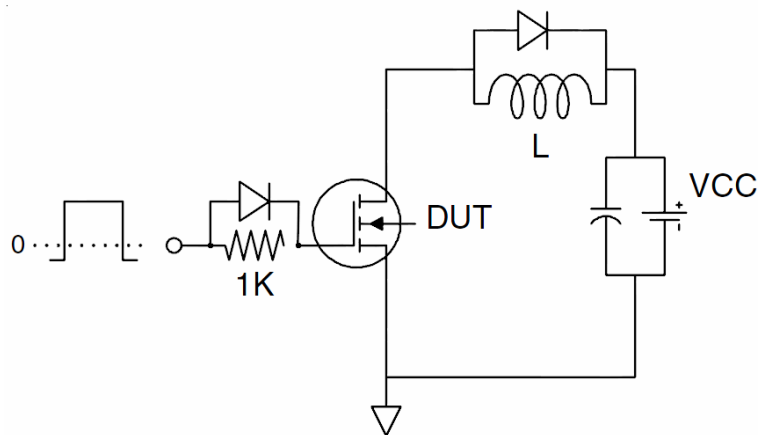
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^\circ\text{C}, V_{DD}=35V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

Test Circuit

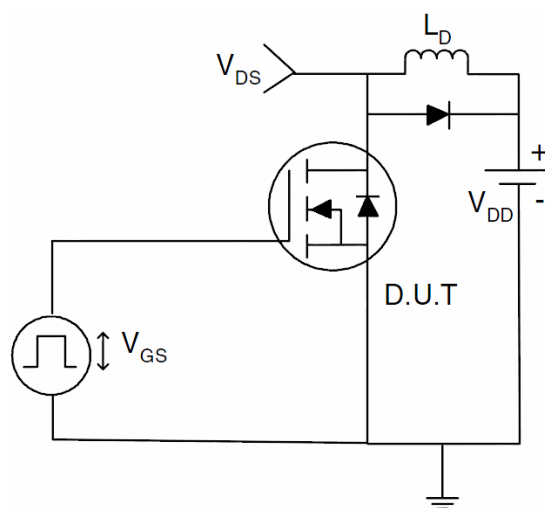
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

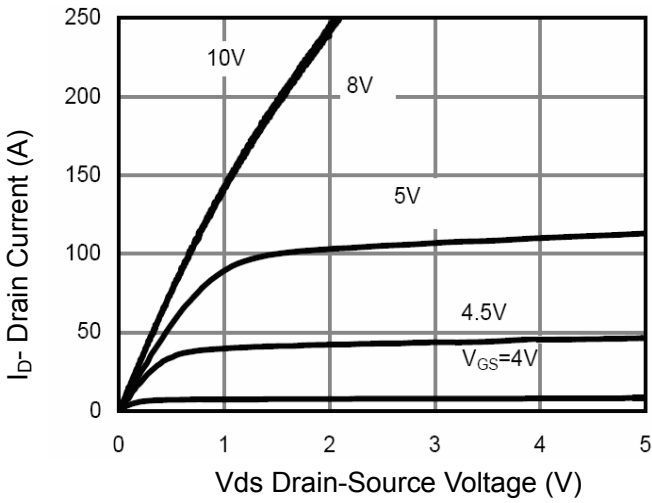


Figure 1 Output Characteristics

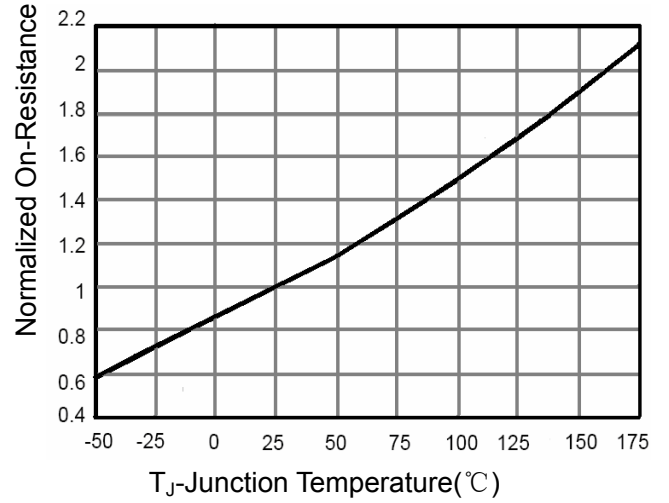


Figure 4 Rdson-Junction Temperature

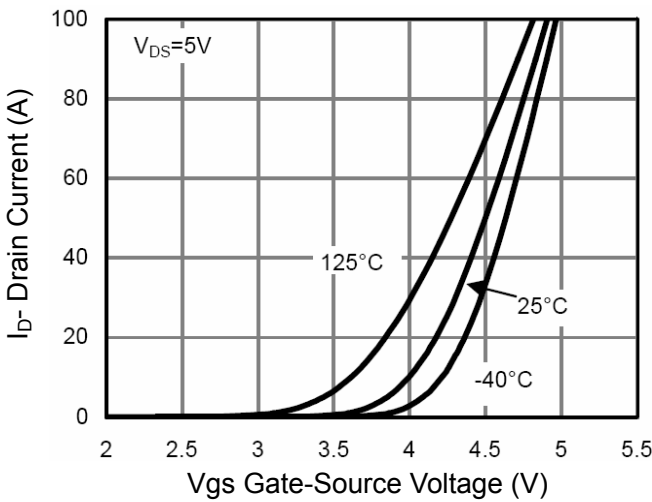


Figure 2 Transfer Characteristics

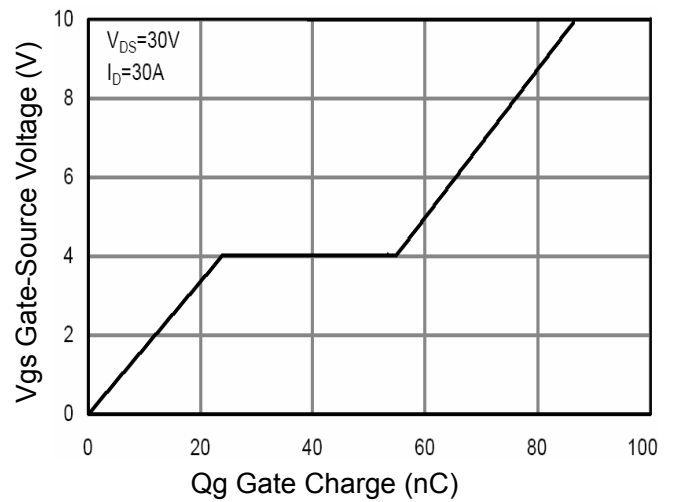


Figure 5 Gate Charge

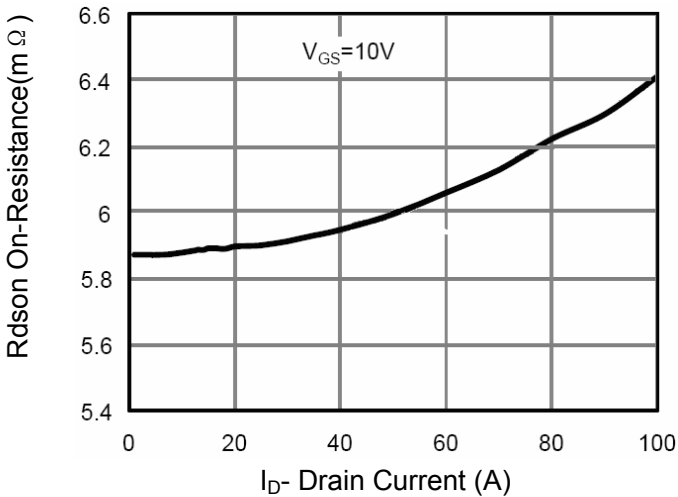


Figure 3 Rdson- Drain Current

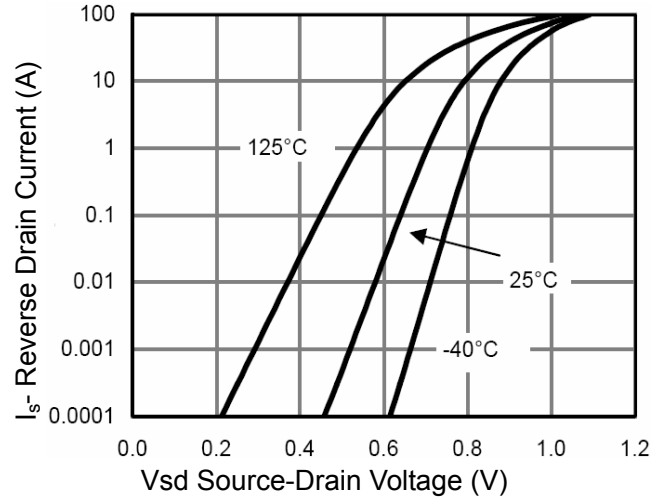


Figure 6 Source- Drain Diode Forward

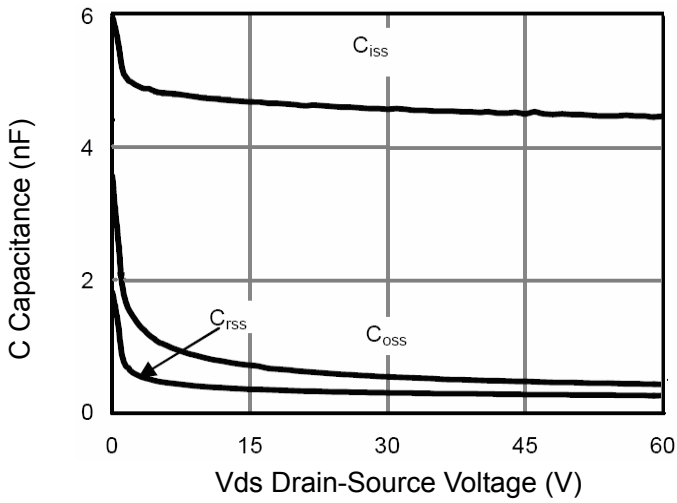


Figure 7 Capacitance vs Vds

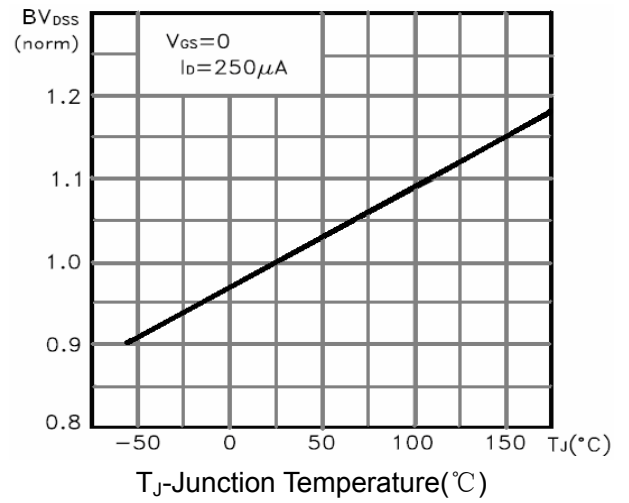


Figure 9 BV_{DSS} vs Junction Temperature

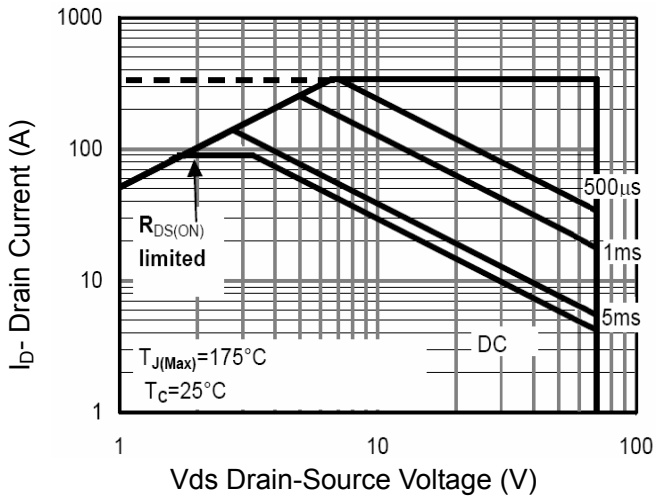


Figure 8 Safe Operation Area

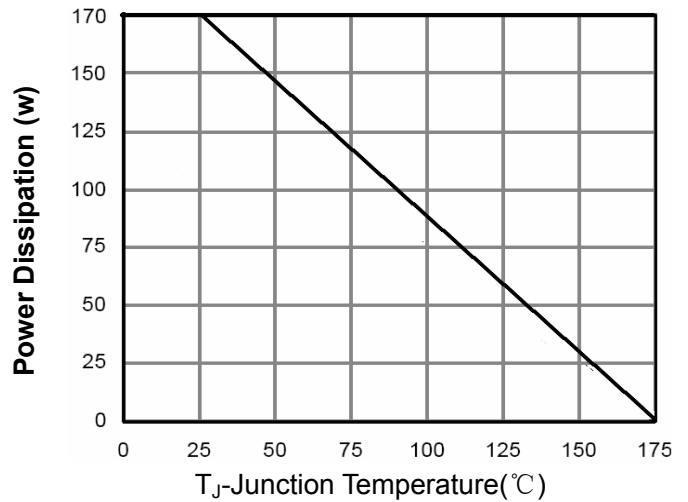


Figure 10 Power De-rating

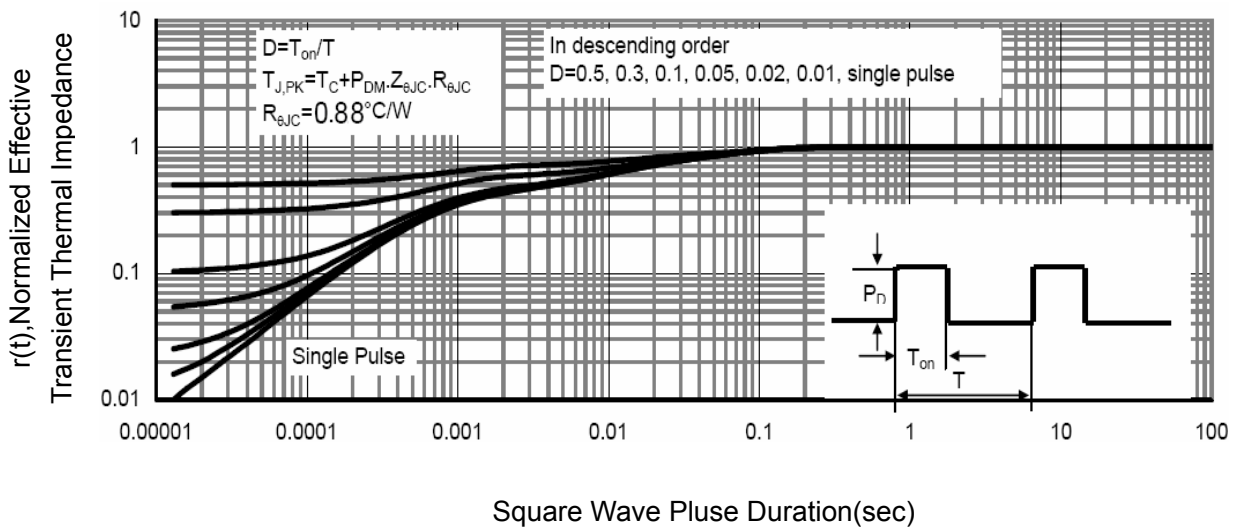
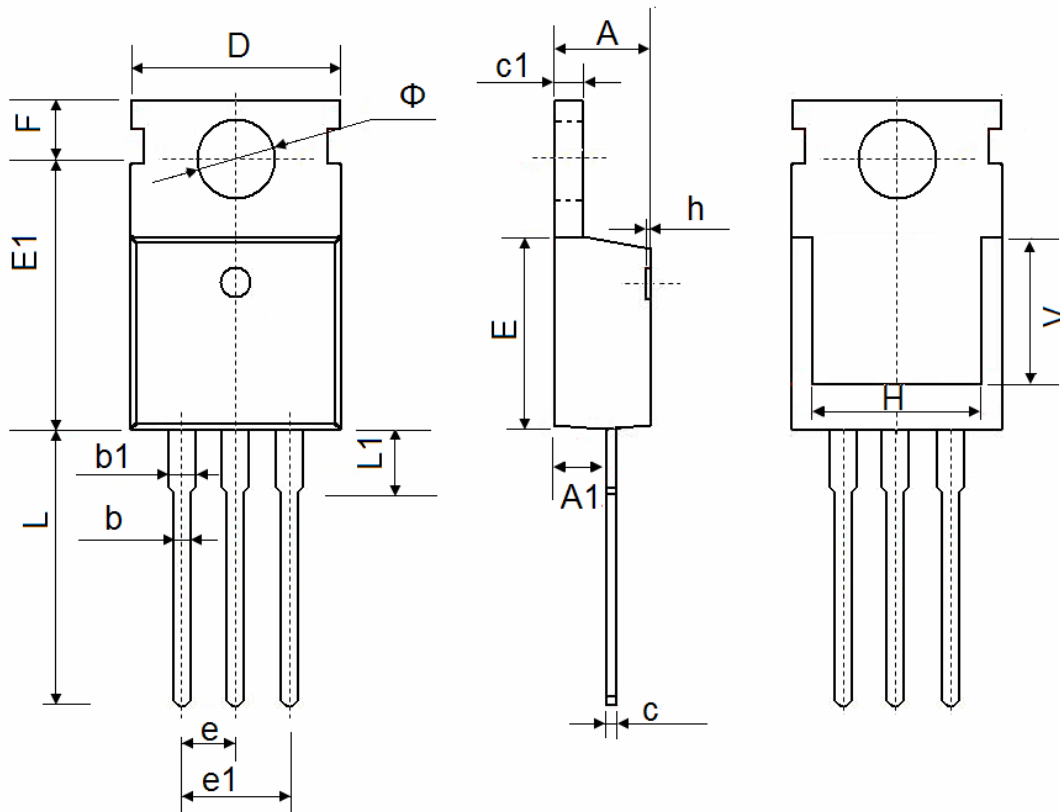


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|--------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.400 | 4.600 | 0.173 | 0.181 |
| A1 | 2.250 | 2.550 | 0.089 | 0.100 |
| b | 0.710 | 0.910 | 0.028 | 0.036 |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 |
| c | 0.330 | 0.650 | 0.013 | 0.026 |
| c1 | 1.200 | 1.400 | 0.047 | 0.055 |
| D | 9.910 | 10.250 | 0.390 | 0.404 |
| E | 8.9500 | 9.750 | 0.352 | 0.384 |
| E1 | 12.650 | 12.950 | 0.498 | 0.510 |
| e | 2.540 TYP. | | 0.100 TYP. | |
| e1 | 4.980 | 5.180 | 0.196 | 0.204 |
| F | 2.650 | 2.950 | 0.104 | 0.116 |
| H | 7.900 | 8.100 | 0.311 | 0.319 |
| h | 0.000 | 0.300 | 0.000 | 0.012 |
| L | 12.900 | 13.400 | 0.508 | 0.528 |
| L1 | 2.850 | 3.250 | 0.112 | 0.128 |
| V | 7.500 REF. | | 0.295 REF. | |
| Φ | 3.400 | 3.800 | 0.134 | 0.150 |